

Customer No.: 31561  
Application No.: 10/710,818  
Docket NO.:14217-US-PA-X

**AMENDMENT**

Please amend the application as indicated hereafter.

**In the Claims :**

**Claim 1 (previously presented)** A n electrostatic discharge (ESD) protection device, comprising:

an ESD protection circuit, comprising:

at least a diode connected in series between a first voltage and a pad; and

at least an ESD component connected in series between a second voltage and a pad, wherein each of the at least an ESD component comprises a deep N-well region formed in a P-type substrate, a triple P-well formed in the deep N-well region, and a highly doped N-type (N+) region and a highly doped P-type (P+) region formed in the triple P-well region.

**Claim 2 (original)** The ESD protection device of claim 1, wherein when a number of the ESD component is one, the N+ region of the ESD component is connected to the pad, and the P+ region of the ESD component is connected to the second voltage.

**Claim 3 (original)** The ESD protection device of claim 1, wherein when a number of the ESD component is two including a 1<sup>st</sup> ESD component and a 2<sup>nd</sup> ESD component, the N+ region of a 1<sup>st</sup> ESD component is connected to the pad, the P+ region of the 2<sup>nd</sup> ESD component is connected to the second voltage, and the P+ region of the 1<sup>st</sup>

Customer No.: 31561  
Application No.: 10/710,818  
Docket NO.:14217-US-PA-X

ESD component is connected to the N+ region of the 2<sup>nd</sup> ESD component.

**Claim 4 (original)** The ESD protection device of claim 1, wherein when a number of the ESD component is S including a 1<sup>st</sup> ESD component to a S<sup>th</sup> ESD component, the N+ region of the 1<sup>st</sup> ESD component is connected to the pad, the P+ region of the S<sup>th</sup> ESD component is connected to the second voltage, and the P+ region of the T<sup>th</sup> ESD component is connected to the N+ region of the (T+1)<sup>th</sup> ESD component, wherein S is a positive integer and T is a positive integer from 1 to S-1.

**Claim 5 (original)** The ESD protection device of claim 1, wherein each of the at least a diode comprises a N-well region formed in a P-type substrate, and a N+ region and a P+ region formed in the N-well region.

**Claim 6 (original)** The ESD protection device of claim 1, wherein when a number of the diode is one, the N+ region of the diode is connected to the first voltage, and the P+ region of the diode is connected to the pad.

**Claim 7 (original)** The ESD protection device of claim 1, wherein when a number of the diode is two including a first diode and a second diode, the N+ region of a first diode is connected to the first voltage, the P+ region of the second diode is connected to the pad, and the P+ region of the first diode is connected to the N+ region of the second diode.

Customer No.: 31561  
Application No.: 10/710,818  
Docket NO.:14217-US-PA-X

**Claim 8 (original)** The ESD protection device of claim 1, wherein when a number of the diode is S including a 1<sup>st</sup> diode to a S<sup>th</sup> diode, the N+ region of the 1<sup>st</sup> diode is connected to the first voltage, the P+ region of the S<sup>th</sup> diode is connected to the pad, and the P+ region of the T<sup>th</sup> diode is connected to the N+ region of the (T+1)<sup>th</sup> diode, wherein S is a positive integer and T is a positive integer from 1 to S-1.

**Claim 9 (previously presented)** The of claim 1, wherein the ESD protection device further comprises another ESD protection circuit comprising:

a PMOS transistor; and

an NMOS transistor, wherein a gate of the PMOS transistor and a gate of the NMOS transistor are connected to the pad, a source of the PMOS transistor is connected to a drain of the NMOS transistor, a drain of the PMOS transistor is connected to the first voltage, and a source of the NMOS transistor is connected to the second voltage.

**Claim 10 (original)** The ESD protection device of claim 1, wherein the ESD protection device is a radio frequency (RF) ESD protection device.

**Claims 11-19 (canceled)**